

SuperMOS – SOT-363 20V BV_{DSS}, 250mΩ R_{DS(on)}, N-channel MOSFET

1. Description

The ES3134KZ is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(on)} with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ES3134KZ is Pb-free.

2. Features

- 20V, R_{DS(on)}=250mΩ(Typ.) @ V_{GS}=4.5V
R_{DS(on)}=320mΩ(Typ.) @V_{GS}=2.5V
R_{DS(on)}=450mΩ(Typ.) @V_{GS}=1.8V
 - Use trench MOSFET technology
 - High density cell design for low R_{DS(on)}
- Material: Halogen free
 - Reliable and rugged
 - Avalanche Rated
 - Low leakage current

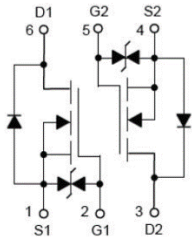
3. Applications

- PWM applications
 - Load switch
- Power management in portable/desktop PCs
 - DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ES3134KZ	SOT-363	.34KZ	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
2	Gate1		
1	Source1		
6	Drain1		
5	Gate2		
4	Source2		
3	Drain2		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	0.88	A
	$T_A=75^{\circ}\text{C}$		0.68	
Maximum Power Dissipation		P_D	0.35	W
Pulsed Drain Current		I_{DM}	3.52	A
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Lead Temperature		T_L	260	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10\text{s}$	$R_{\theta JA}$		357	$^{\circ}\text{C/W}$

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±10V			±10	uA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	0.35	0.75	1.1	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =0.5A		250	330	mΩ
		V _{GS} =2.5V, I _D =0.4A		320	430	
		V _{GS} =1.8V, I _D =0.2A		450	730	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, f=1MHz, V _{DS} =10V		33		pF
Output Capacitance	C _{OSS}			20		
Reverse Transfer Capacitance	C _{RSS}			10		
Total Gate Charge	Q _{G(TOT)}	V _{GS} =4.5V, V _{DS} =10V, I _D =0.5A		0.8		nC
Gate-to-Source Charge	Q _{GS}			0.3		
Gate-to-Drain Charge	Q _{GD}			0.15		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =4.5V, V _{DS} =10V, I _D =0.5A, R _G =10Ω		4		ns
Rise Time	t _r			18.8		
Turn-Off Delay Time	t _{d(OFF)}			10		
Fall Time	t _f			23		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =0.5A			1.5	V

7. Typical Characteristic

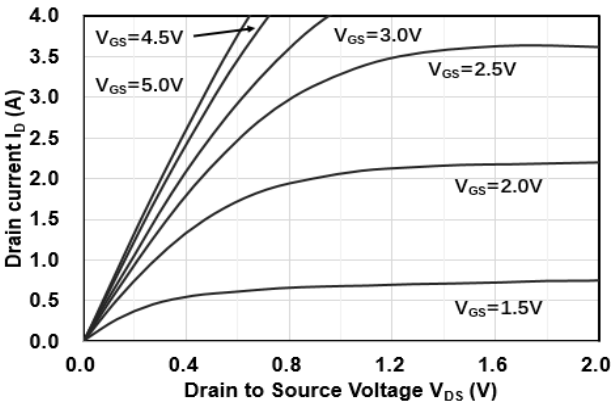


Figure1. Output Characteristics

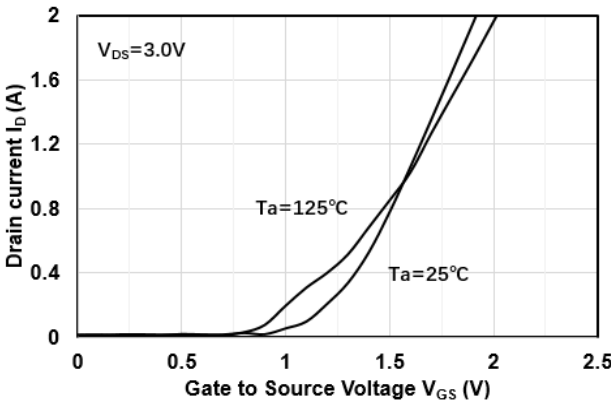


Figure2. Transfer Characteristics

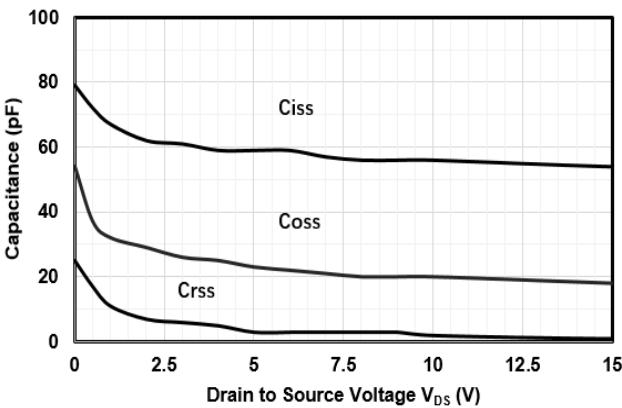


Figure3. Capacitance Characteristics

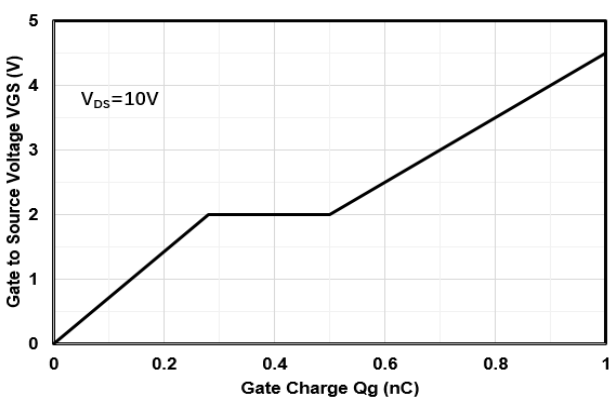


Figure4. Gate Charge

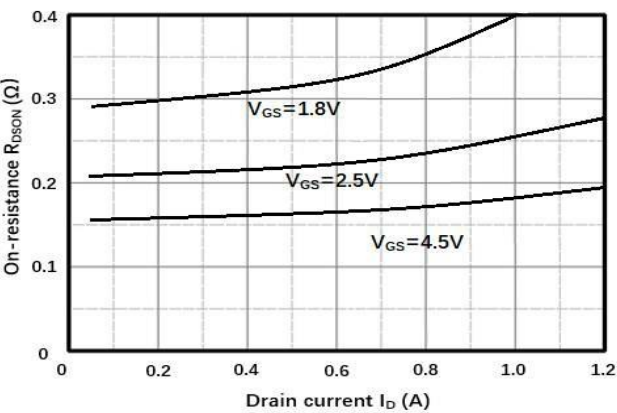


Figure5. Drain-Source on Resistance

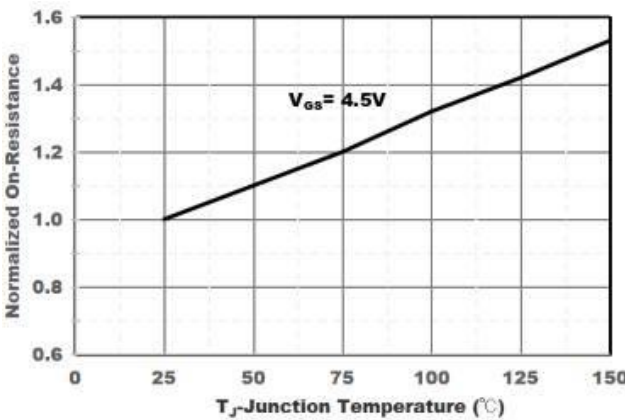


Figure6. Drain-Source on Resistance

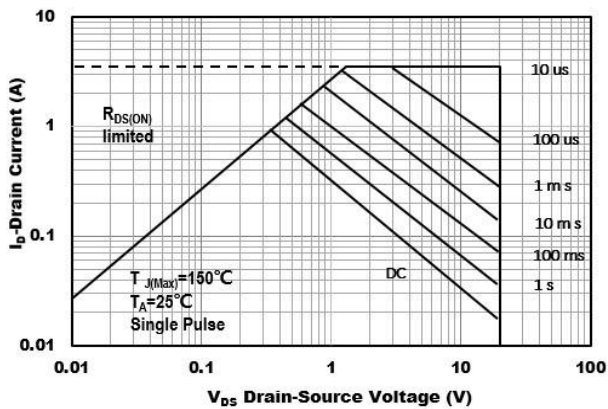
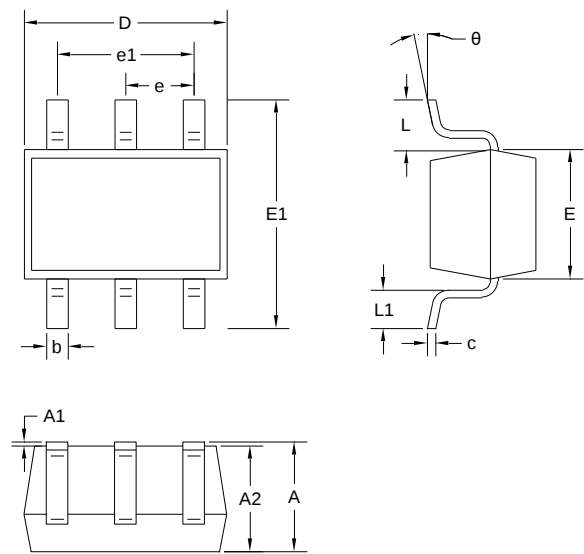


Figure7. Safe Operation Area

8. Dimension (SOT-363)



Unit: mm

Symbol		A	A1	A2	b	c	D	θ
Spec	Min	0.85	0	0.85	0.15	0.08	2.00	0°
	Max	1.05	0.10	0.95	0.35	0.15	2.20	8°
Symbol		E	E1	e	e1	L	L1	-
Spec	Min	1.15	2.10	0.650	1.200	0.525	0.2600	-
	Max	1.35	2.40	REF	1.400	REF	0.4600	-

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